NCV8402, NCV8402A

Self-Protected Low Side Driver with Temperature and Current Limit

NCV8402/A is a three terminal protected Low−Side Smart Discrete device. The protection features include overcurrent, overtemperature, ESD and integrated Drain−to−Gate clamping for overvoltage protection. This device offers protection and is suitable for harsh automotive environments.

Features

- Short−Circuit Protection
- Thermal Shutdown with Automatic Restart
- Overvoltage Protection
- Integrated Clamp for Inductive Switching
- ESD Protection
- dV/dt Robustness
- Analog Drive Capability (Logic Level Input)
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free and are RoHS Compliant

Typical Applications

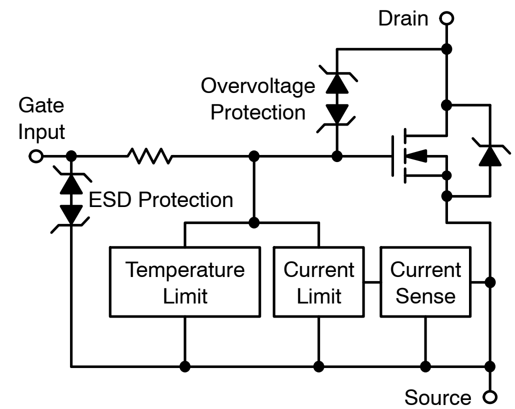
- Switch a Variety of Resistive, Inductive and Capacitive Loads
- Can Replace Electromechanical Relays and Discrete Circuits
- Automotive / Industrial

ON Semiconductor®

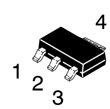
http://onsemi.com

$V_{(BR)DSS}$ (Clamped)	$R_{DS(ON)}$ TYP	I_D MAX
42 V	165 mΩ @ 10 V	2.0 A*

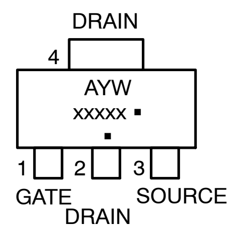
*Max current limit value is dependent on input condition.



MARKING DIAGRAM



SOT−223
CASE 318E
STYLE 3



A	= Assembly Location
Y	= Year
W	= Work Week
xxxxx	= V8402 or 8402A
▪	= Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NCV8402STT1G	SOT−223 (Pb−Free)	1000/Tape & Reel
NCV8402ASTT1G		
NCV8402STT3G	SOT−223 (Pb−Free)	4000/Tape & Reel
NCV8402ASTT3G		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating		Symbol	Value	Unit
Drain−to−Source Voltage Internally Clamped		V_{DSS}	42	V
Drain−to−Gate Voltage Internally Clamped	(R_G = 1.0 MΩ)	V_{DGR}	42	V
Gate−to−Source Voltage		V_{GS}	±14	V
Continuous Drain Current		I_D	Internally Limited	
Power Dissipation	@ T_A = 25°C (Note 1) @ T_A = 25°C (Note 2) @ T_T = 25°C (Note 1)	P_D	1.1 1.7 8.9	W
Thermal Resistance	Junction−to−Ambient Steady State (Note 1) Junction−to−Ambient Steady State (Note 2) Junction−to−Tab Steady State (Note 1)	$R_{\theta JA}$ $R_{\theta JA}$ $R_{\theta JT}$	114 72 14	°C/W
Single Pulse Drain−to−Source Avalanche Energy (V_{DD} = 32 V, V_G = 5.0 V, I_{PK} = 1.0 A, L = 300 mH, $R_{G(ext)}$ = 25 Ω)		E_{AS}	150	mJ
Load Dump Voltage	(V_{GS} = 0 and 10 V, R_I = 2.0 Ω, R_L = 9.0 Ω, t_d = 400 ms)	V_{LD}	87	V
Operating Junction Temperature		T_J	−40 to 150	°C
Storage Temperature		T_{stg}	−55 to 150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.
1. Surface−mounted onto min pad FR4 PCB, (2 oz. Cu, 0.06″ thick).
2. Surface−mounted onto 2″ sq. FR4 board (1″ sq., 1 oz. Cu, 0.06″ thick).

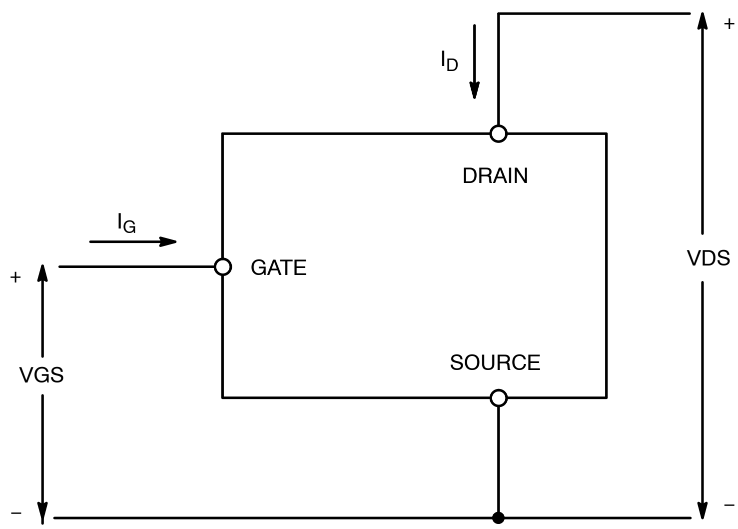


Figure 1. Voltage and Current Convention

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage (Note 3)	V_{GS} = 0 V, I_D = 10 mA, T_J = 25°C	$V_{(BR)DSS}$	42	46	55	V
	V_{GS} = 0 V, I_D = 10 mA, T_J = 150°C (Note 5)		40	45	55	
Zero Gate Voltage Drain Current	V_{GS} = 0 V, V_{DS} = 32 V, T_J = 25°C	I_{DSS}		0.25	4.0	μA
	V_{GS} = 0 V, V_{DS} = 32 V, T_J = 150°C (Note 5)			1.1	20	
Gate Input Current	V_{DS} = 0 V, V_{GS} = 5.0 V	I_{GSSF}		50	100	μA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 150 μA	$V_{GS(th)}$	1.3	1.8	2.2	V
Gate Threshold Temperature Coefficient		$V_{GS(th)}/T_J$		4.0		−mV/°C
Static Drain−to−Source On−Resistance	V_{GS} = 10 V, I_D = 1.7 A, T_J = 25°C	$R_{DS(on)}$		165	200	mΩ
	V_{GS} = 10 V, I_D = 1.7 A, T_J = 150°C (Note 5)			305	400	
	V_{GS} = 5.0 V, I_D = 1.7 A, T_J = 25°C			195	230	
	V_{GS} = 5.0 V, I_D = 1.7 A, T_J = 150°C (Note 5)			360	460	
	V_{GS} = 5.0 V, I_D = 0.5 A, T_J = 25°C			190	230	
	V_{GS} = 5.0 V, I_D = 0.5 A, T_J = 150°C (Note 5)			350	460	
Source−Drain Forward On Voltage	V_{GS} = 0 V, I_S = 7.0 A	V_{SD}		1.0		V
SWITCHING CHARACTERISTICS (Note 5)						
Turn−ON Time (10% V_{IN} to 90% I_D)	V_{GS} = 10 V, V_{DD} = 12 V I_D = 2.5 A, R_L = 4.7 Ω	t_{ON}		25		μs
Turn−OFF Time (90% V_{IN} to 10% I_D)		t_{OFF}		120		
Slew−Rate ON (70% V_{DS} to 50% V_{DS})	V_{GS} = 10 V, V_{DD} = 12 V, R_L = 4.7 Ω	$-dV_{DS}/dt_{ON}$		0.8		V/μs
Slew−Rate OFF (50% V_{DS} to 70% V_{DS})		dV_{DS}/dt_{OFF}		0.3		
SELF PROTECTION CHARACTERISTICS (T_J = 25°C unless otherwise noted) (Note 4)						
Current Limit	V_{DS} = 10 V, V_{GS} = 5.0 V, T_J = 25°C	I_{LIM}	3.7	4.3	5.0	A
	V_{DS} = 10 V, V_{GS} = 5.0 V, T_J = 150°C (Note 5)		2.3	3.0	3.7	
	V_{DS} = 10 V, V_{GS} = 10 V, T_J = 25°C		4.2	4.8	5.4	
	V_{DS} = 10 V, V_{GS} = 10 V, T_J = 150°C (Note 5)		2.7	3.6	4.5	
Temperature Limit (Turn−off)	V_{GS} = 5.0 V (Note 5)	$T_{LIM(off)}$	150	175	200	°C
Thermal Hysteresis	V_{GS} = 5.0 V	$\Delta T_{LIM(on)}$		15		
Temperature Limit (Turn−off)	V_{GS} = 10 V (Note 5)	$T_{LIM(off)}$	150	165	185	
Thermal Hysteresis	V_{GS} = 10 V	$\Delta T_{LIM(on)}$		15		
GATE INPUT CHARACTERISTICS (Note 5)						
Device ON Gate Input Current	V_{GS} = 5 V I_D = 1.0 A	I_{GON}		50		μA
	V_{GS} = 10 V I_D = 1.0 A			400		
Current Limit Gate Input Current	V_{GS} = 5 V, V_{DS} = 10 V	I_{GCL}		0.05		mA
	V_{GS} = 10 V, V_{DS} = 10 V			0.4		
Thermal Limit Fault Gate Input Current	V_{GS} = 5 V, V_{DS} = 10 V	I_{GTL}		0.15		mA
	V_{GS} = 10 V, V_{DS} = 10 V			0.7		
ESD ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) (Note 5)						
Electro−Static Discharge Capability	Human Body Model (HBM)	ESD	4000			V
	Machine Model (MM)		400			

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
4. Fault conditions are viewed as beyond the normal operating range of the part.
5. Not subject to production testing.

TYPICAL PERFORMANCE CURVES

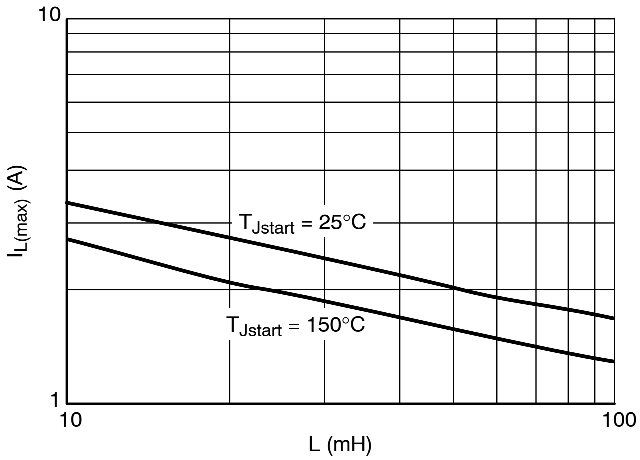


Figure 2. Single Pulse Maximum Switch−off Current vs. Load Inductance

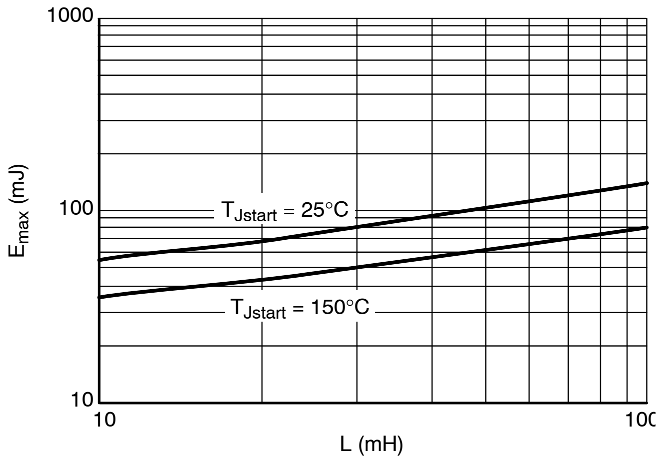


Figure 3. Single Pulse Maximum Switching Energy vs. Load Inductance

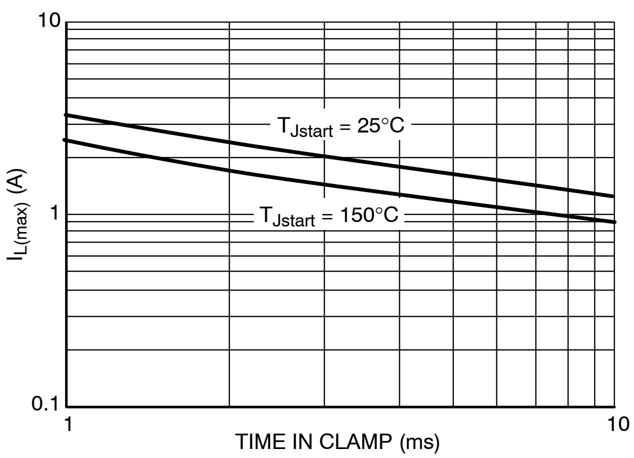


Figure 4. Single Pulse Maximum Inductive Switch−off Current vs. Time in Clamp

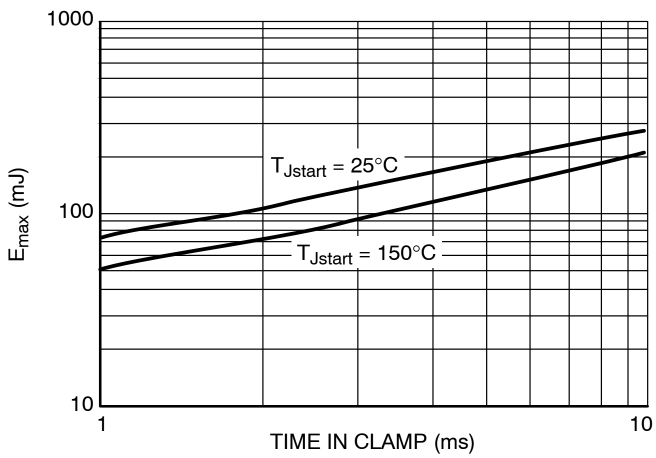


Figure 5. Single Pulse Maximum Inductive Switching Energy vs. Time in Clamp

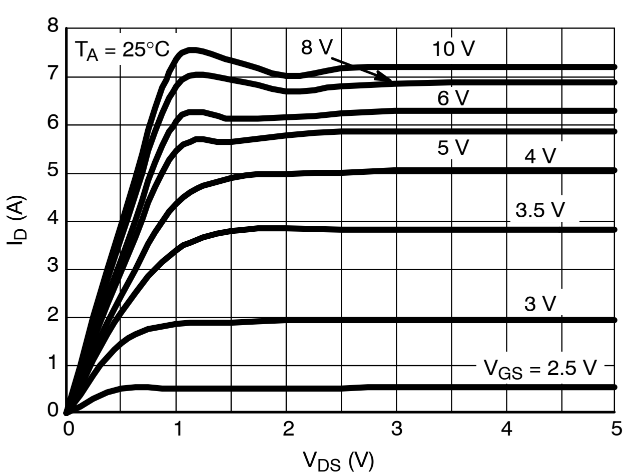


Figure 6. On−state Output Characteristics

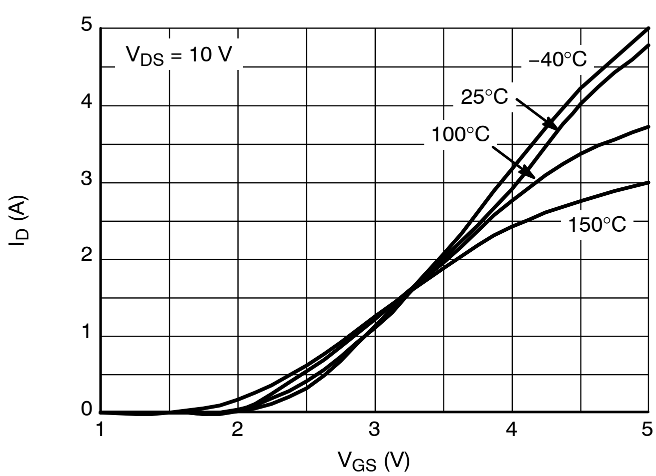


Figure 7. Transfer Characteristics

TYPICAL PERFORMANCE CURVES

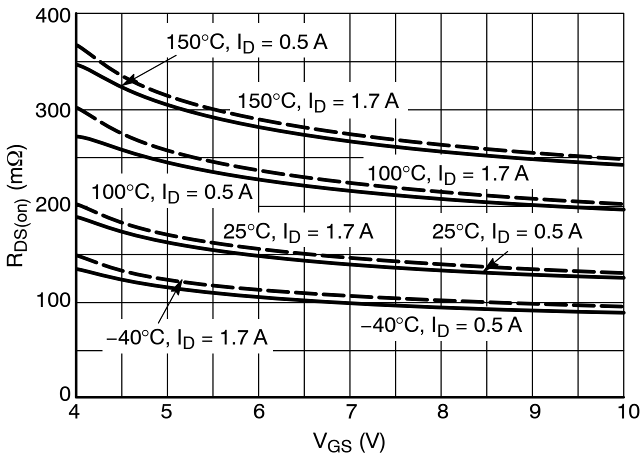


Figure 8. $R_{DS(on)}$ vs. Gate−Source Voltage

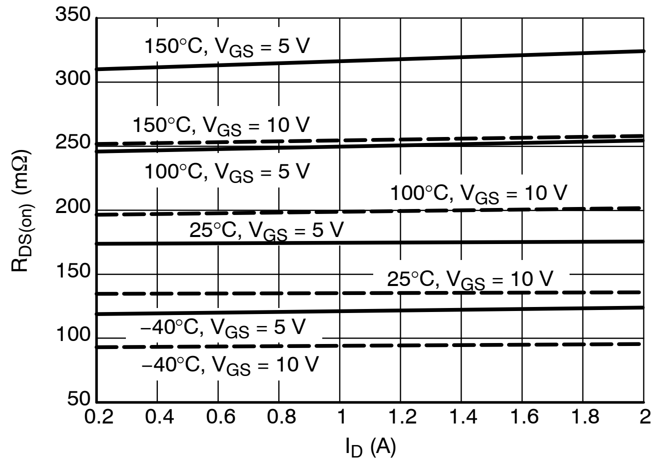


Figure 9. $R_{DS(on)}$ vs. Drain Current

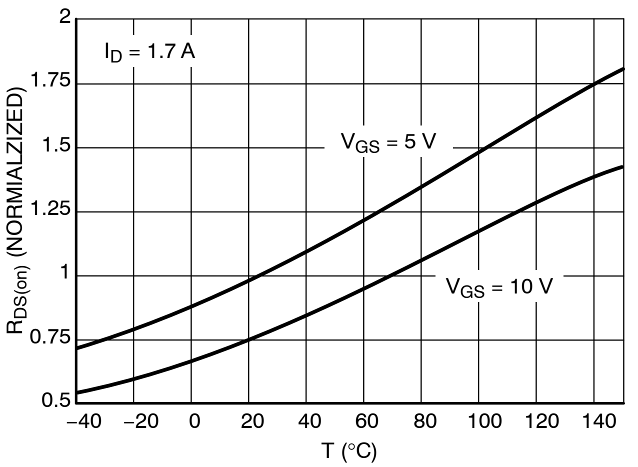


Figure 10. Normalized $R_{DS(on)}$ vs. Temperature

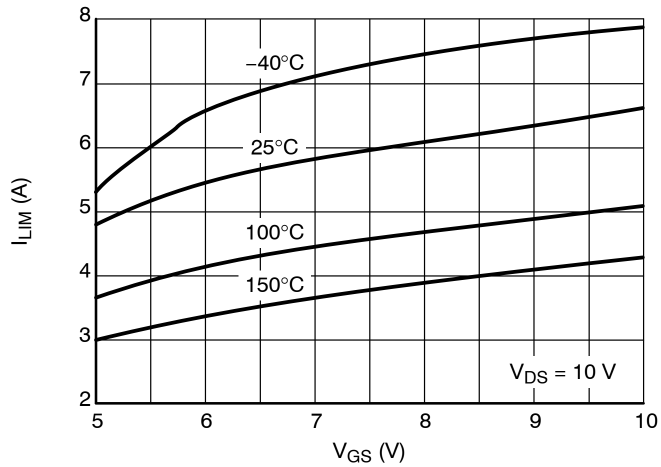


Figure 11. Current Limit vs. Gate−Source Voltage

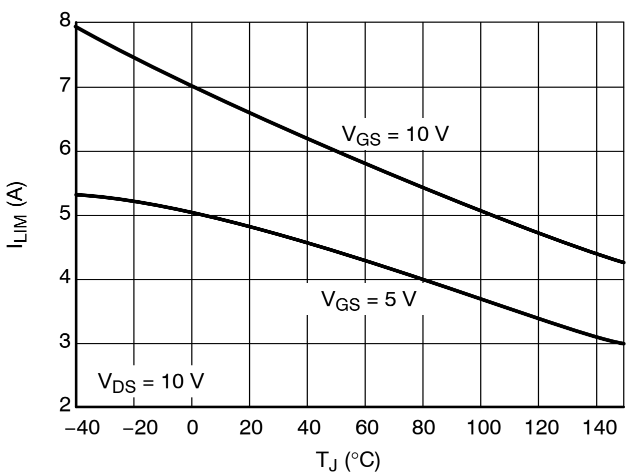


Figure 12. Current Limit vs. Junction Temperature

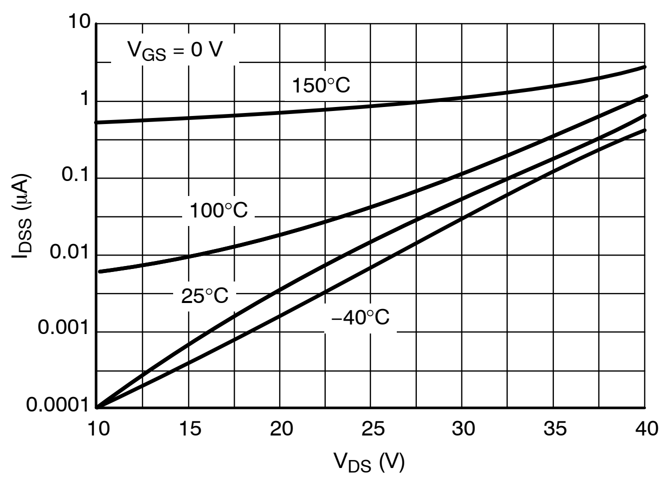


Figure 13. Drain−to−Source Leakage Current

TYPICAL PERFORMANCE CURVES

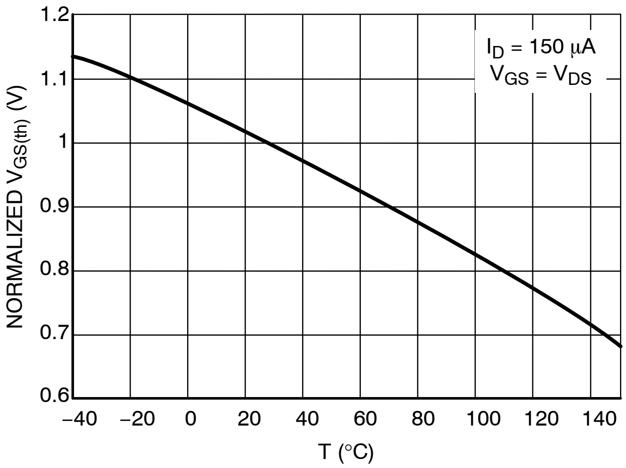


Figure 14. Normalized Threshold Voltage vs. Temperature

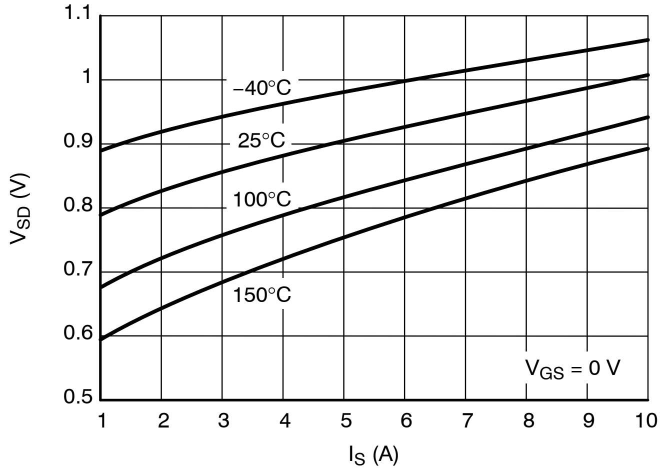


Figure 15. Source−Drain Diode Forward Characteristics

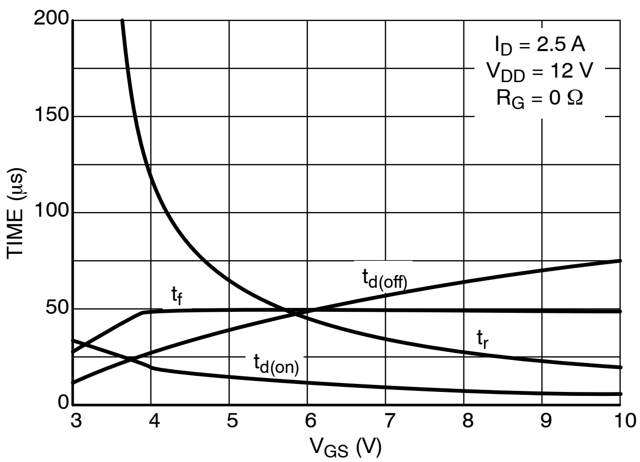


Figure 16. Resistive Load Switching Time vs. Gate−Source Voltage

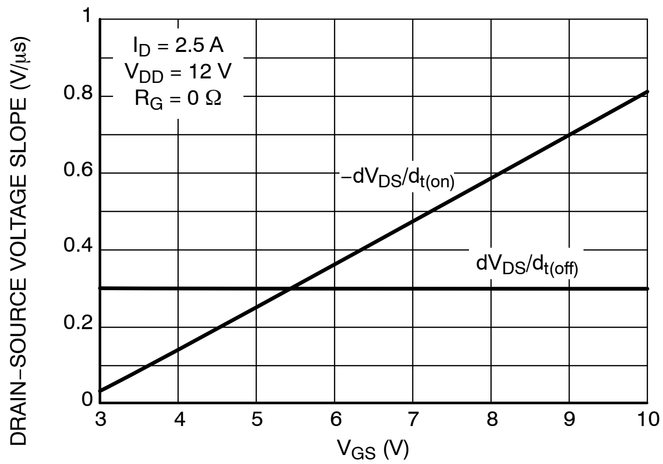


Figure 17. Resistive Load Switching Drain−Source Voltage Slope vs. Gate−Source Voltage

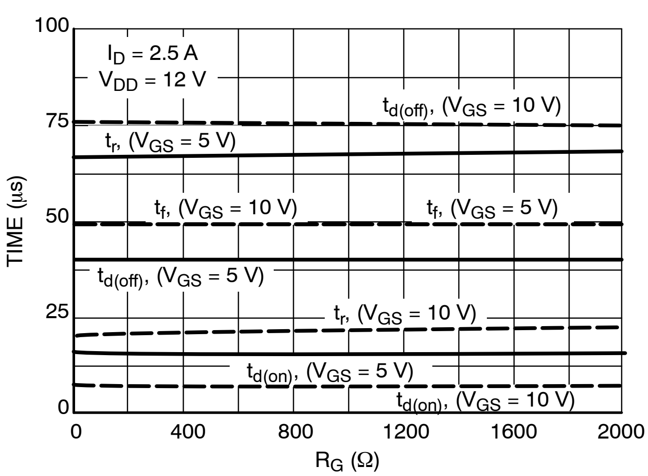


Figure 18. Resistive Load Switching Time vs. Gate Resistance

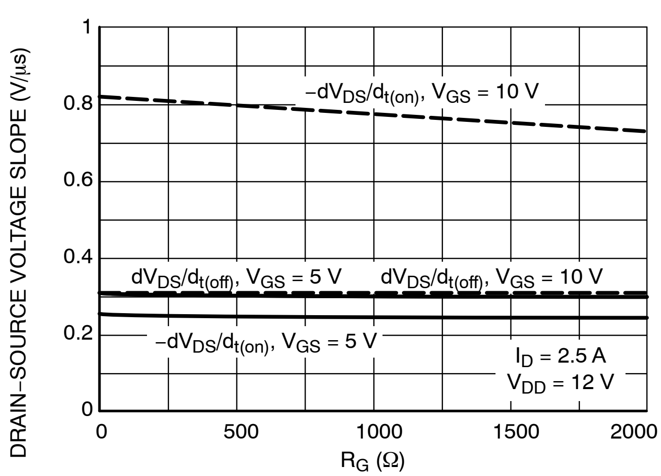


Figure 19. Drain−Source Voltage Slope during Turn On and Turn Off vs. Gate Resistance

TYPICAL PERFORMANCE CURVES

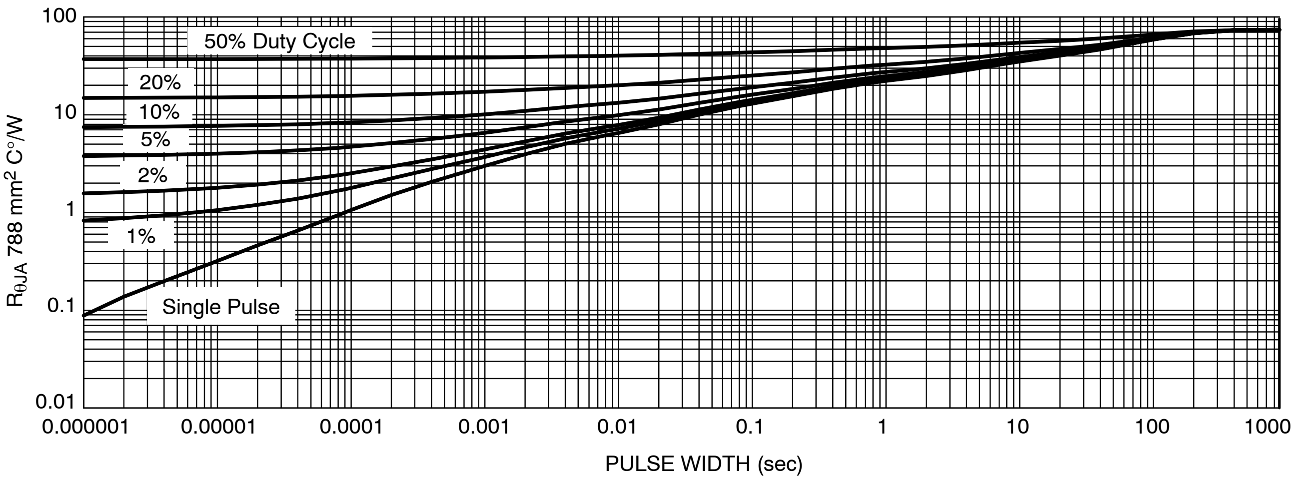


Figure 20. Transient Thermal Resistance

TEST CIRCUITS AND WAVEFORMS

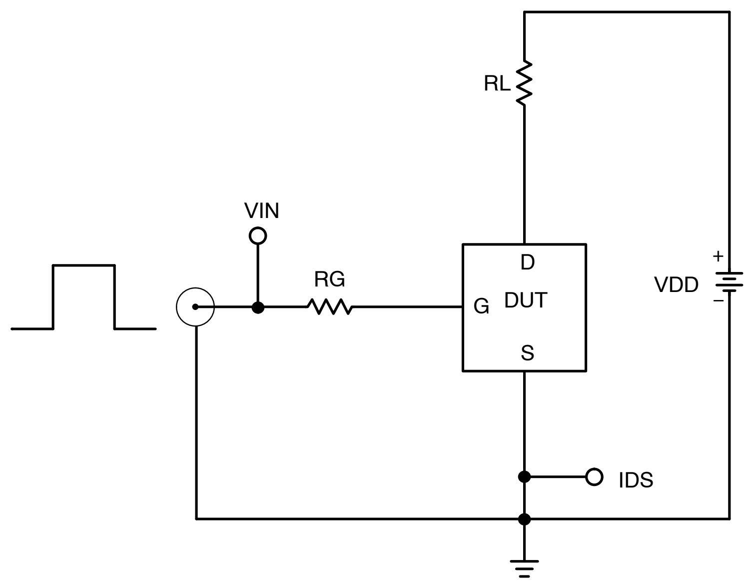


Figure 21. Resistive Load Switching Test Circuit

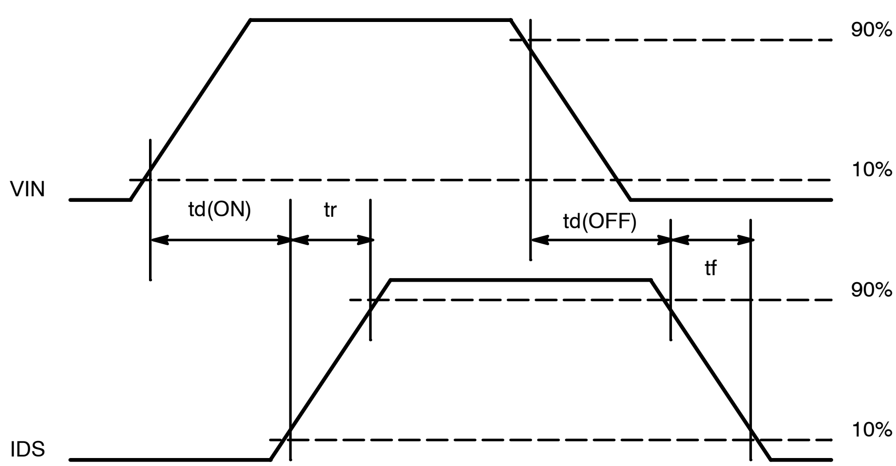


Figure 22. Resistive Load Switching Waveforms

TEST CIRCUITS AND WAVEFORMS

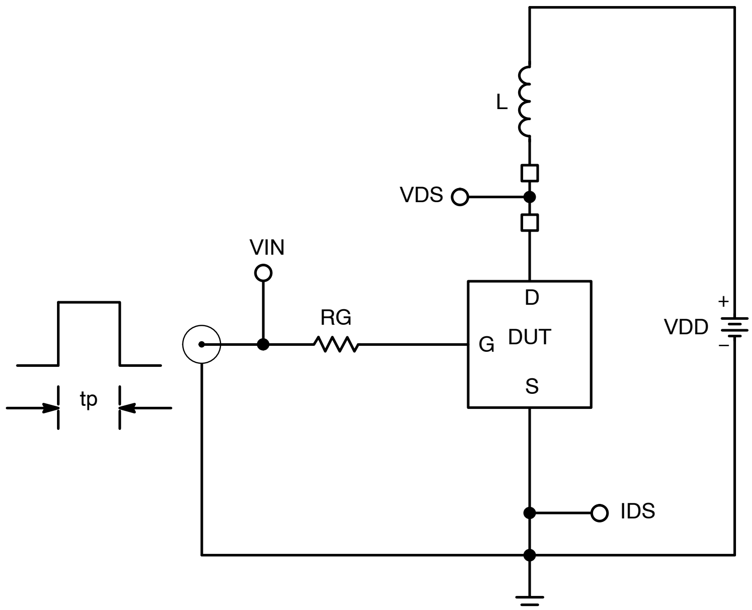


Figure 23. Inductive Load Switching Test Circuit

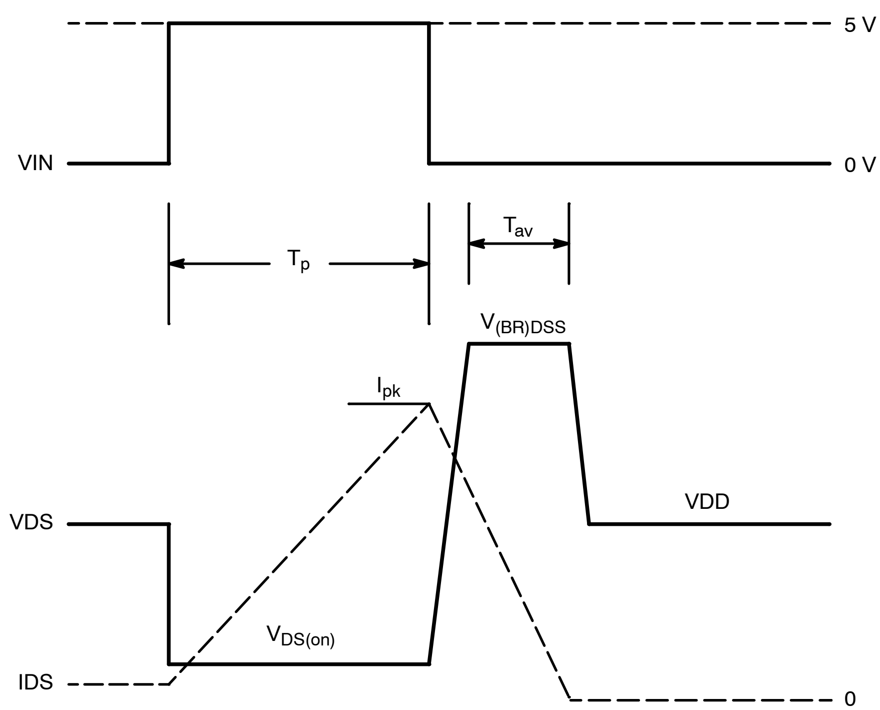
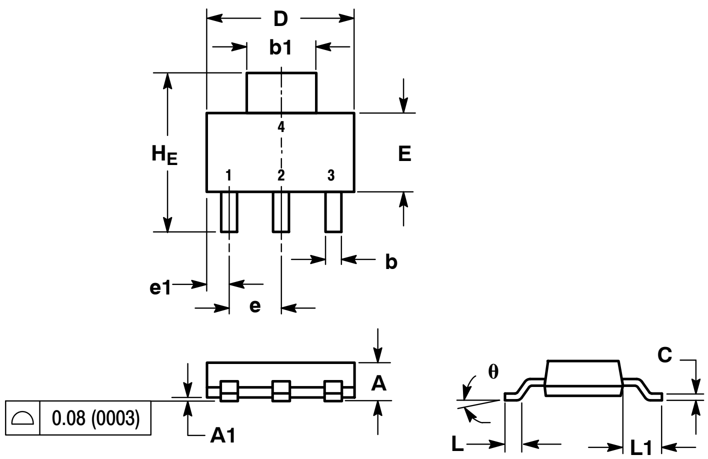


Figure 24. Inductive Load Switching Waveforms

PACKAGE DIMENSIONS

SOT−223 (TO−261)
CASE 318E−04
ISSUE N

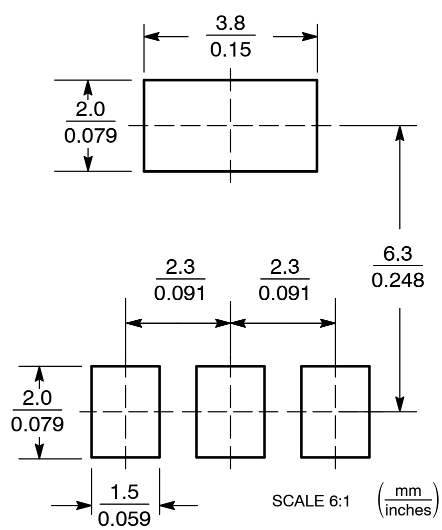


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20	−−−	−−−	0.008	−−−	−−−
L1	1.50	1.75	2.00	0.060	0.069	0.078
H_E	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	–	10°	0°	–	10°

STYLE 3:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT



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